



IRFP31N50LPBF Information



For Reference Only

Part Number IRFP31N50LPBF
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 31A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFP31N50LPBF Specifications

Manufacturer Part Number IRFP31N50LPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 210nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 460W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 19A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3 Report errors?		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)460W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Package	TO-247-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)460W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)460W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)460W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)460W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	31A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 19A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 5000pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 19A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)460W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	210nC @ 10V
FET Feature - Gower Dissipation (Max) 460W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 19A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	5000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 19A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 180 mOhm @ 19A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Power Dissipation (Max)	460W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	180 mOhm @ 19A, 10V
Supplier Device Package TO-247-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

IRFP31N50LPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFP31N50LPBF Payment Methods



















IRFP31N50LPBF Shipping Methods













If you have any question about IRFP31N50LPBF, please do not hesitate to contact us!

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